

Small switching (60V, 10A)

2SK2095N

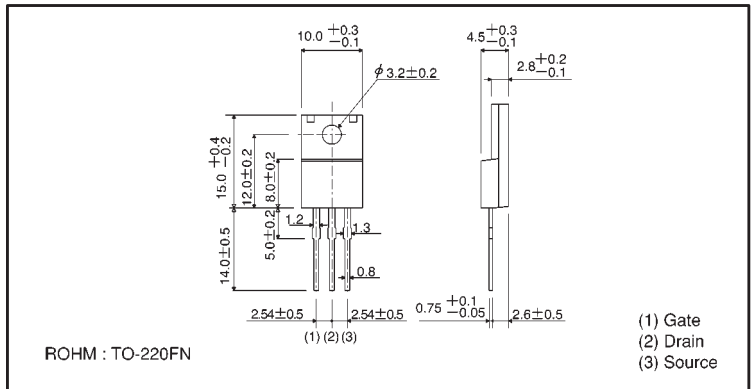
●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Wide SOA (safe operating area).
- 4) Easily designed drive circuits.
- 5) Low $V_{GS(th)}$.
- 6) Easy to parallel.

●Structure

Silicon N-channel
MOSFET

●External dimensions (Units: mm)



●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V_{DSS}	60	V
Gate-source voltage	V_{GSS}	± 20	V
Drain current	Continuous	I_D	10 A
	Pulsed	I_{DP}^*	40 A
Reverse drain current	Continuous	I_{DR}	10 A
	Pulsed	I_{DRP}^*	40 A
Total power dissipation ($T_c=25^\circ\text{C}$)	P_D	30	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ\text{C}$

* $P_w \leq 10 \mu\text{s}$, Duty cycle $\leq 1\%$

●Packaging specifications

Type	Package	Bulk
	Code	—
	Basic ordering unit (pieces)	500
2SK2095N		○

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Gate-source leakage	I _{GSS}	—	—	±100	nA	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR)DSS}	60	—	—	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	—	—	100	μA	V _{DS} =60V, V _{GS} =0V
Gate threshold voltage	V _{GS(th)}	1.0	—	2.5	V	V _{DS} =10V, I _D =1mA
Static drain-source on-state resistance	R _{DS(on)}	—	0.080	0.095	Ω	I _D =5A, V _{GS} =10V
		—	0.11	0.14		I _D =5A, V _{GS} =4V
Forward transfer admittance	Y _{fs} *	5.0	—	—	S	I _D =5A, V _{DS} =10V
Input capacitance	C _{iss}	—	1600	—	pF	V _{DS} =10V
Output capacitance	C _{oss}	—	600	—	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	—	150	—	pF	f=1MHz
Turn-on delay time	t _{d(on)}	—	30	—	ns	I _D =5A, V _{DD} ≠30V
Rise time	t _r	—	80	—	ns	V _{GS} =10V
Turn-off delay time	t _{d(off)}	—	300	—	ns	R _L =6Ω
Fall time	t _f	—	100	—	ns	R _G =10Ω

* P_w≤300 μs, Duty cycle≤1%

●Electrical characteristic curves

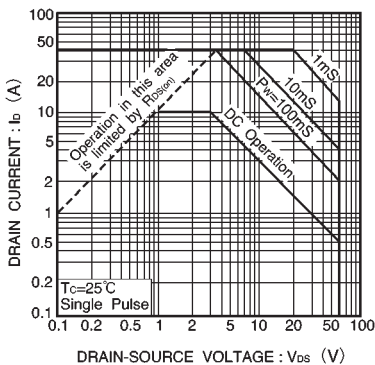


Fig.1 Maximum safe operating area

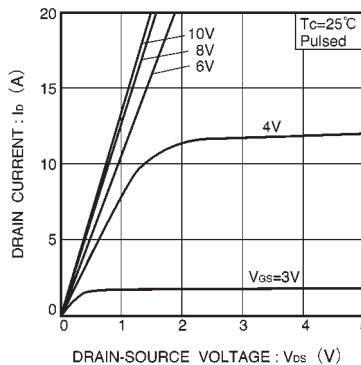


Fig.2 Typical output characteristics

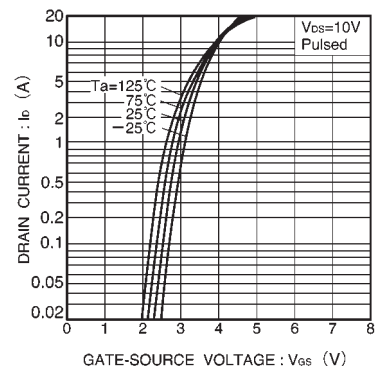


Fig.3 Typical transfer characteristics

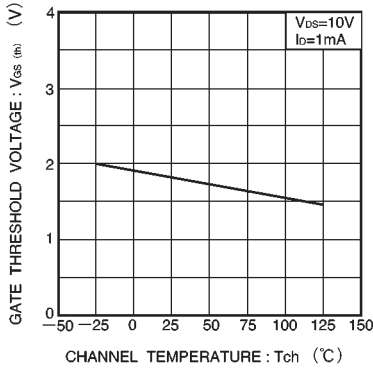


Fig.4 Gate threshold voltage vs. channel temperature

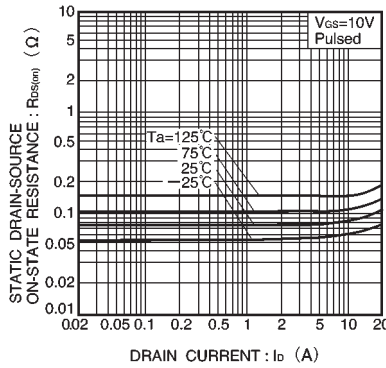


Fig.5 Static drain-source on-state resistance vs. drain current (I)

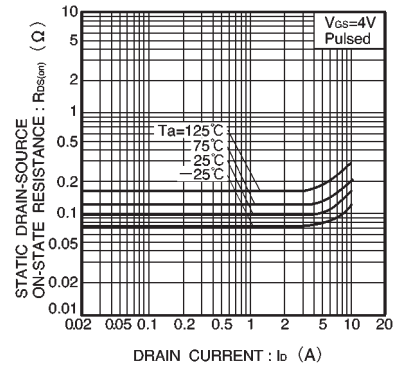


Fig.6 Static drain-source on-state resistance vs. drain current (II)

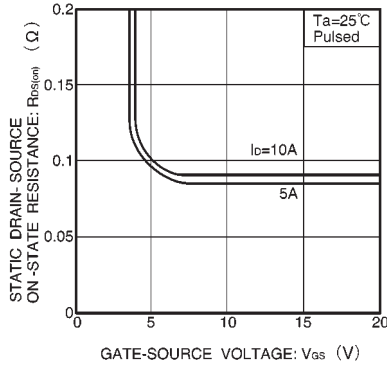


Fig.7 Static drain-source on-state resistance vs. gate-source voltage

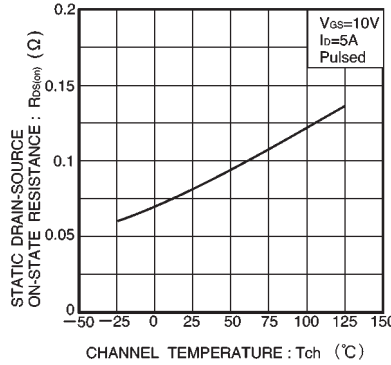


Fig.8 Static drain-source on-state resistance vs. channel temperature

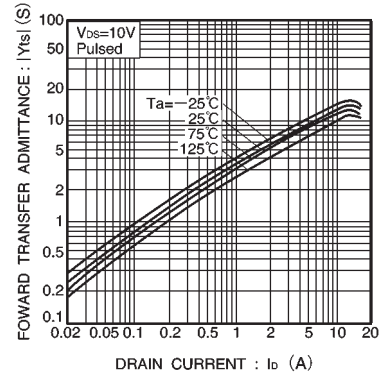


Fig.9 Forward transfer admittance vs. drain current

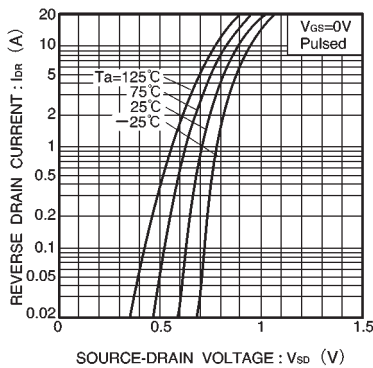


Fig.10 Reverse drain current vs. source-drain voltage (I)

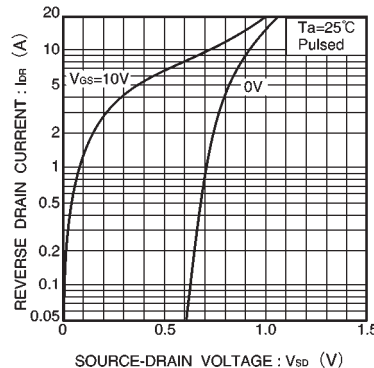


Fig.11 Reverse drain current vs. source-drain voltage (II)

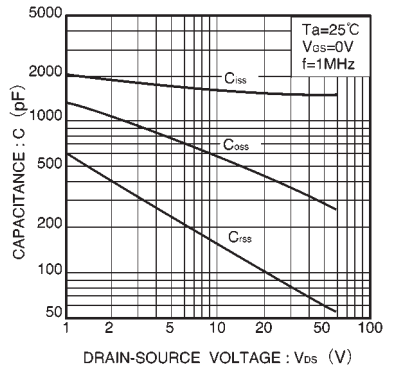


Fig.12 Typical capacitance vs. drain-source voltage

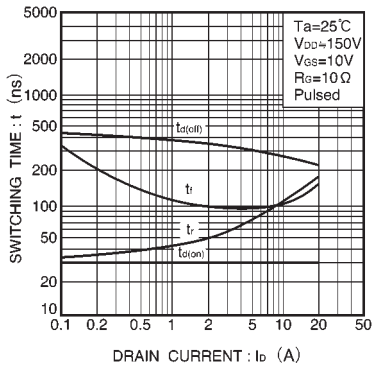


Fig.13 Switching characteristics
(See Figures 15 and 16 for the measurement circuit and resultant waveforms.)

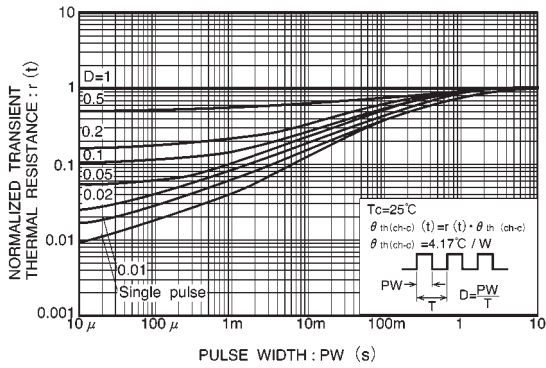


Fig.14 Normalized transient thermal resistance vs. pulse width

● Switching characteristics measurement circuit

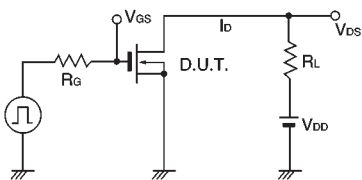


Fig.15 Switching time measurement circuit

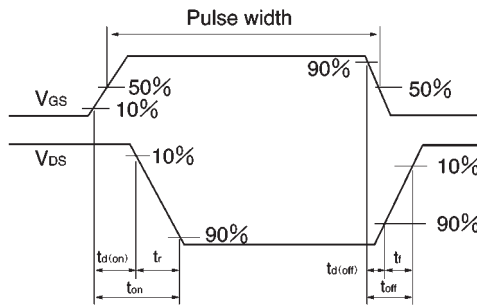


Fig.16 Switching time waveforms